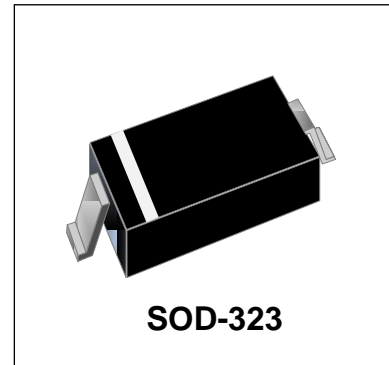




## Features

- 63 Watts Peak Pulse Power per Line ( $t_p=8/20\mu s$ )
- Protects five I/O lines
- Low Clamping Voltage
- Working Voltage: 5V
- Low Leakage Current
- AEC-Q101 Qualified



## IEC Compatibility (EN61000-4)

- IEC 61000-4-2 (ESD)  $\pm 25kV$  (air),  $\pm 25kV$  (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4.5A (8/20 $\mu s$ )

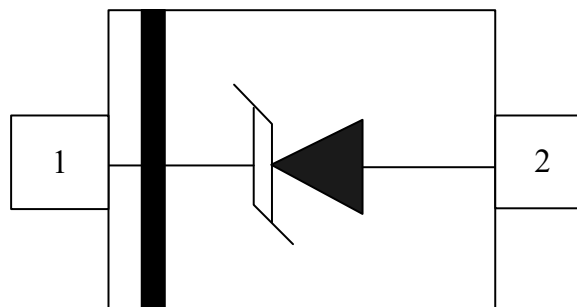
## Mechanical Characteristics

- SOD-323 package
- Marking: Marking Code
- Packaging: Tape and Reel
- RoHS Compliant

## Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras

## Schematic & PIN Configuration

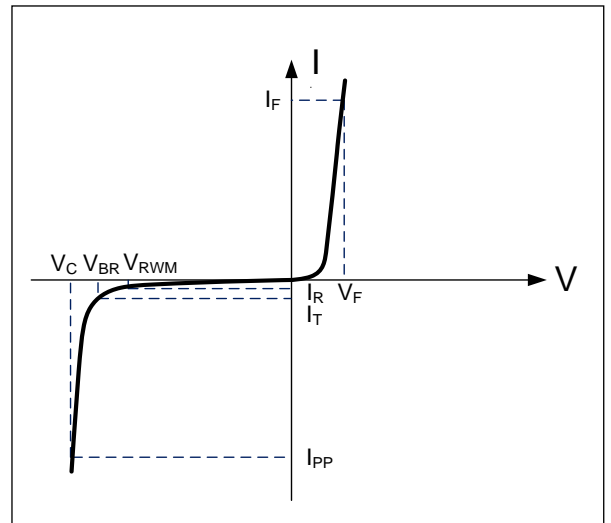


SOD-323 (Top View)

<b>Absolute Maximum Rating</b>			
Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p=8/20\mu s$ )	$P_{PP}$	63	W
Peak Pulse Current ( $t_p=8/20\mu s$ )	$I_{PP}$	4.5	A
Operating Temperature	$T_J$	-55 to + 125	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 to +150	$^{\circ}C$

### Electrical Parameters (T=25 $^{\circ}C$ )

Symbol	Parameter
$I_{PP}$	Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Reverse Stand-Off Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



### Electrical Characteristics

<b>DW05D3D-AT-E</b>						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1mA$	6		9	V
Reverse Leakage Current	$I_R$	$V_{RWM}=5V, T=25^{\circ}C$			500	nA
Forward Voltage	$V_F$	$I_F=10mA$	0.5		1	V
Clamping Voltage	$V_C$	$I_{PP}=4.5A, t_p=8/20\mu s$		11	14	V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP}=4A$ $t_p=0.2/100ns$		9.7		V
ESD Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP}=16A$ $t_p=0.2/100ns$		15.1		V
Dynamic Resistance <sup>1,2</sup>	$R_{DYN}$	$TLP=0.2/100ns$		0.45		$\Omega$
Junction Capacitance	$C_j$	$V_R=0V, f=1MHz$		28		pF

**Note:** 1、TLP Setting :  $t_p=100ns, t_r=0.2ns, I_{TLP}$  and  $V_{TLP}$  sample window:  $t_1=70ns$  to  $t_2=90ns$ .

2、Dynamic resistance calculated from  $I_{PP}=4A$  to  $I_{PP}=16A$  using "Best Fit"

## Typical Characteristics

Figure 1: Peak Pulse Power Vs Pulse Time

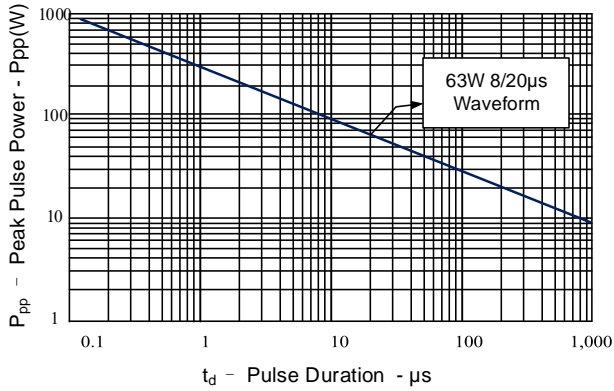


Figure 2: Power Derating Curve

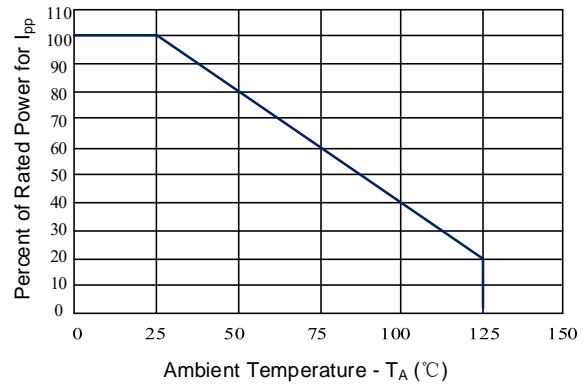


Figure 3: Clamping Voltage vs. Peak Pulse Current

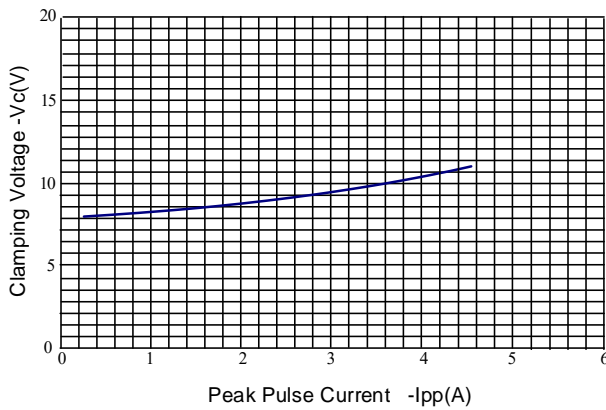


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

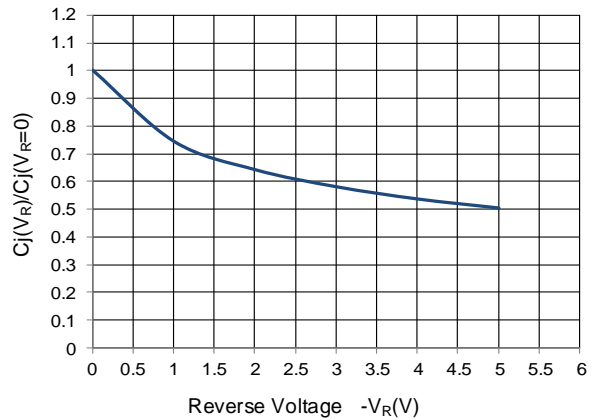


Figure 5: TLP Positive I-V Curve

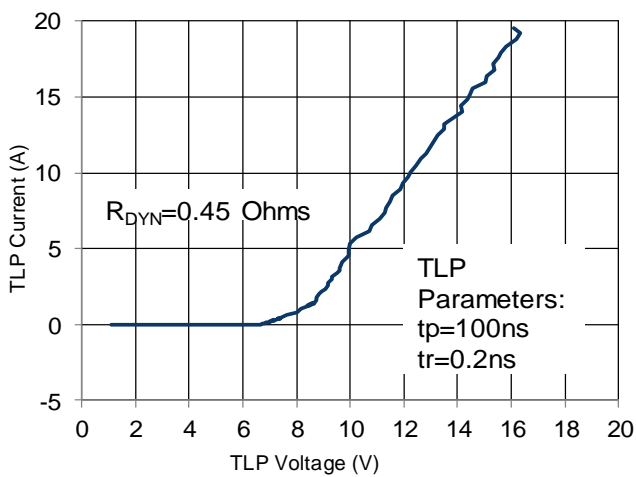
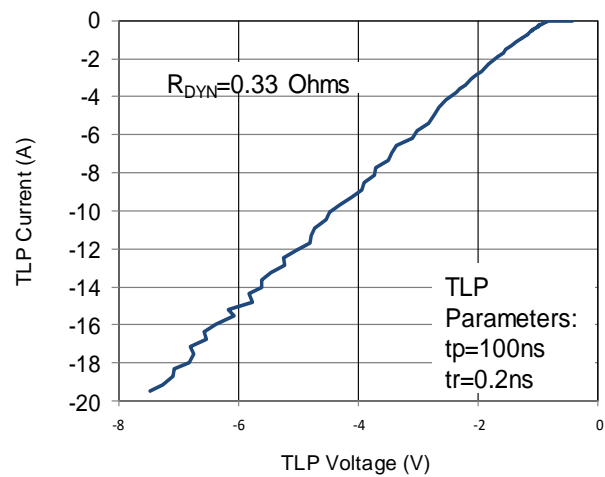


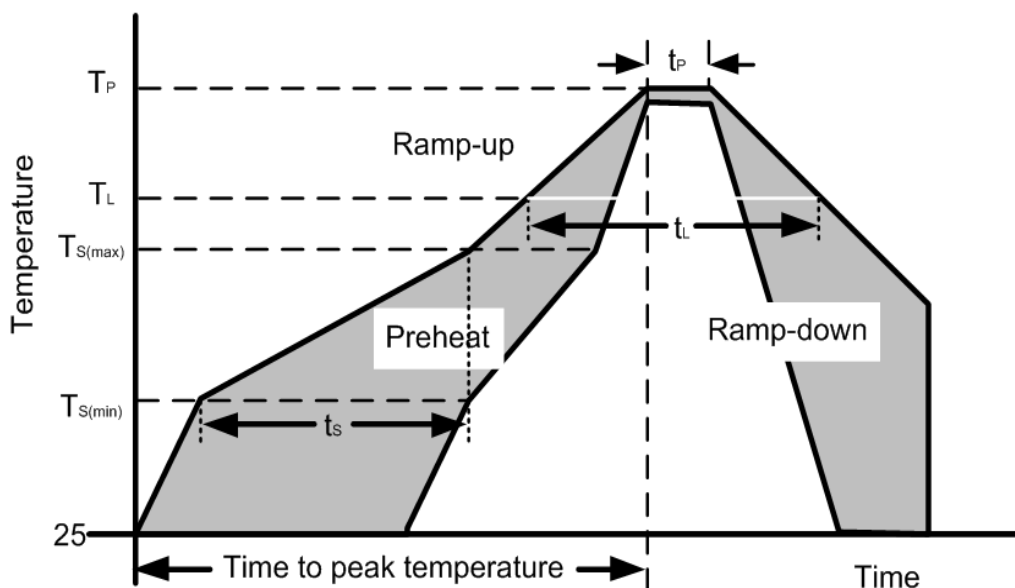
Figure 6: TLP Negative I-V Curve



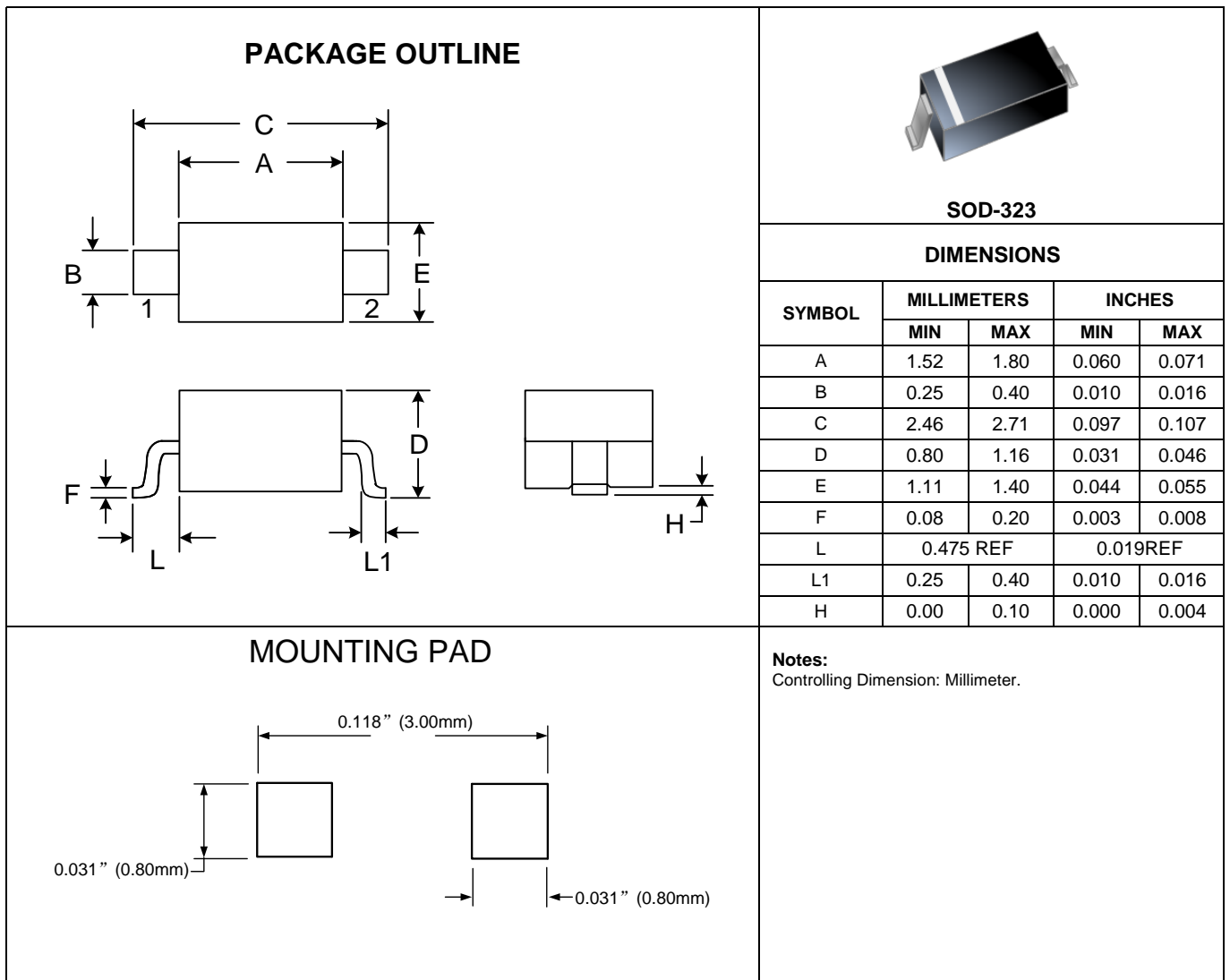


### Soldering Parameters


Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ( $T_{S(min)}$ )	150°C
	Temperature Max ( $T_{S(max)}$ )	200°C
	Time (min to max) ( $t_s$ )	60 – 190 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{S(max)}$ to $T_L$ — Ramp-up Rate		5°C/second max
Reflow	Temperature ( $T_L$ ) (Liquidus)	217°C
	Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_P$ )		260+0/-5 °C
Time within actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_P$ )		8 minutes Max.
Do not exceed		280°C



## Outline Drawing – SOD-323



## Marking Codes

Part Number	Marking Code
DW05D3D-AT-E	

## Package Information

Qty: 3k/Reel